

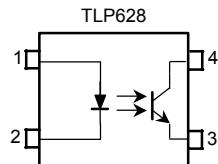
TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP628,TLP628-2,TLP628-4

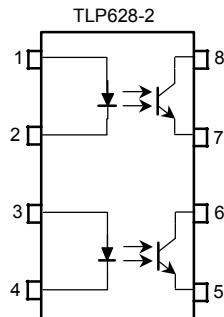
Programmable Controllers
DC-Output Module
Telecommunication

The TOSHIBA TLP628, -2, and -4 consists of a gallium arsenide infrared emitting diode optically coupled to a phototransistor which has a 350V high voltage of collector-emitter breakdown voltage. The TLP628-2 offers two isolated channels in a eight lead plastic DIP package, while the TLP628-4 provide four isolated channels per package.

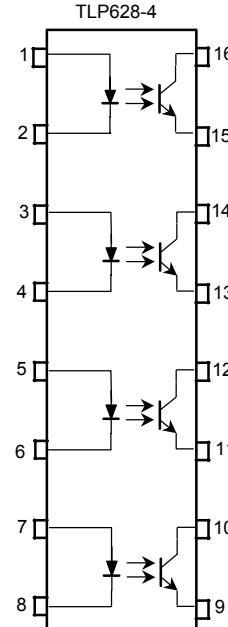
- Collector-emitter voltage: 350 V (min.)
- Current transfer ratio: 50% (min.)
- Isolation voltage: 5000VRms (min.)
- UL recognized: UL1577, file No. E67349

Pin Configurations (top view)

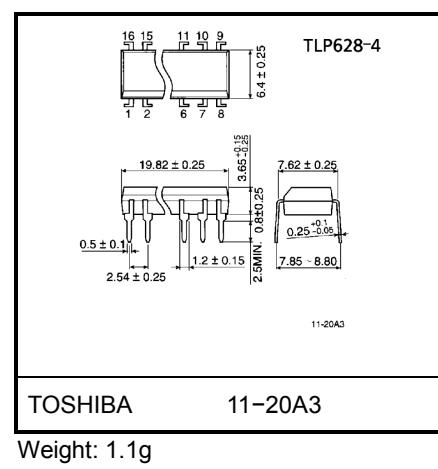
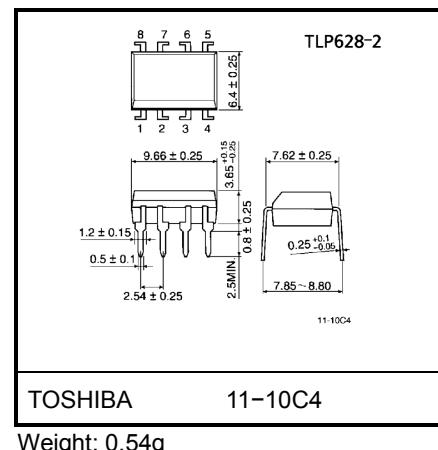
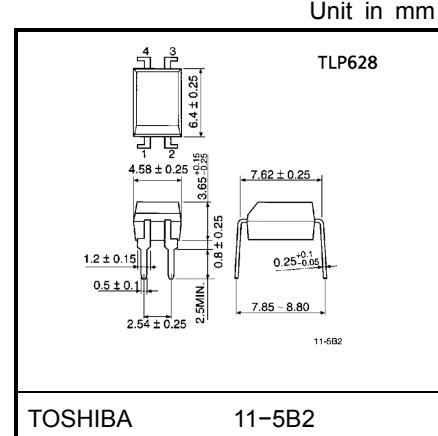
1: Anode
2: Cathode
3: Emitter
4: Collector



1, 3: Anode
2, 4: Cathode
5, 7: Emitter
6, 8: Collector



1, 3, 5, 7: Anode
2, 4, 6, 8: Cathode
9, 11, 13, 15: Emitter
10, 12, 14, 16: Collector



Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating		Unit
			TLP628	TLP628-2 TLP628-4	
LED	Forward current	I _F	60	50	mA
	Forward current derating	ΔI _F / °C	-0.7 (Ta ≥ 39°C)	-0.5 (Ta ≥ 25°C)	mA / °C
	Pulse forward current	I _{FP}	1 (100μs pulse, 100pps)		A
	Reverse voltage	V _R	5		V
	Junction temperature	T _j	125		°C
Detector	Collector-emitter voltage	V _{CCEO}	350		V
	Emitter-collector voltage	V _{ECO}	7		V
	Collector current	I _C	50		mA
	Collector power dissipation (1 circuit)	P _C	150	100	mW
	Collector power dissipation derating (Ta ≥ 25°C, 1 circuit)	ΔP _C / °C	-1.5	-1.0	mW / °C
	Junction temperature	T _j	125		°C
	Storage temperature range	T _{stg}	-55~125		°C
	Operating temperature range	T _{opr}	-55~100		°C
	Lead soldering temperature	T _{sol}	260 (10s)		°C
	Total package power dissipation (1 circuit)	P _T	200	150	mW
	Total package power dissipation derating (Ta ≥ 25°C, 1 circuit)	ΔP _T / °C	-2.0	-1.5	mW / °C
Isolation voltage		B _{VS}	5000 (AC, 1min., R.H. ≤ 60%) (Note 1)		Vrms

(Note 1) Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V _{CC}	—	—	200	V
Forward current	I _F	—	16	25	mA
Collector current	I _C	—	—	10	mA
Operating temperature	T _{opr}	-25	—	85	°C

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5 V	—	—	10	µA
	Capacitance	C _T	V = 0, f = 1 MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage	V _{(BR) CEO}	I _C = 0.1 mA	350	—	—	V
	Emitter-collector breakdown voltage	V _{(BR) ECO}	I _E = 0.1 mA	7	—	—	V
	Collector dark current	I _{CEO}	V _{CE} = 300 V	—	10	200	nA
			V _{CE} = 300 V, Ta = 85°C	—	—	50	µA
	Capacitance collector to emitter	C _{CE}	V = 0, f = 1 MHz	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	I _C / I _F (sat)	I _F = 1 mA, V _{CE} = 0.4 V Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 2.4 mA, I _F = 8 mA	—	—	0.4	V
		I _C = 0.2 mA, I _F = 1 mA Rank GB	—	0.2	—	
			—	—	0.4	

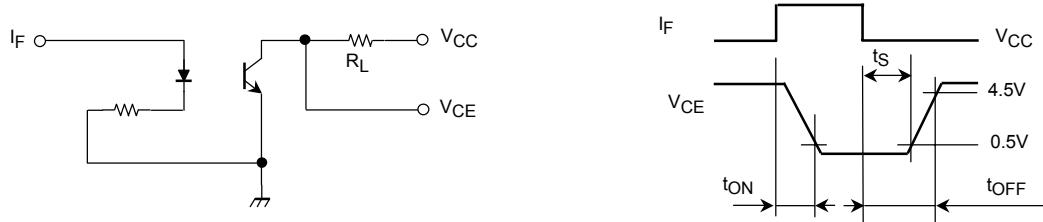
Isolation Characteristics (Ta = 25°C)

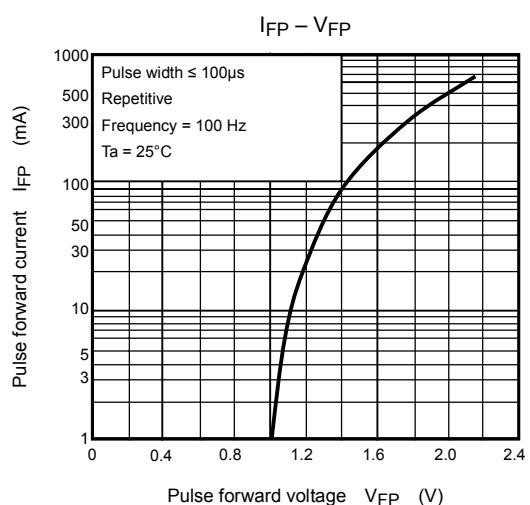
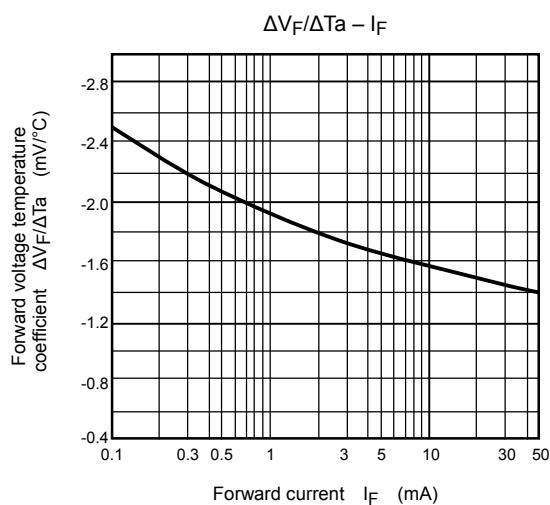
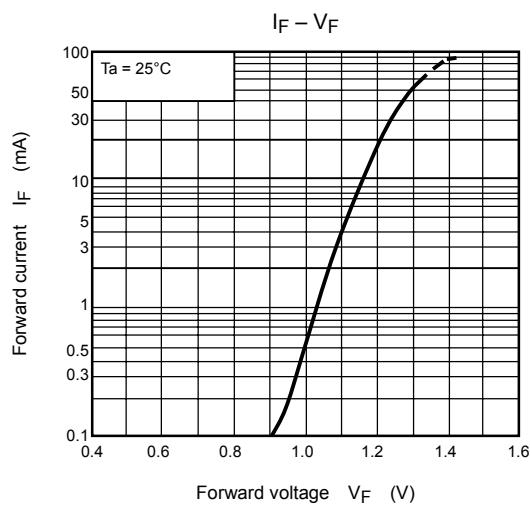
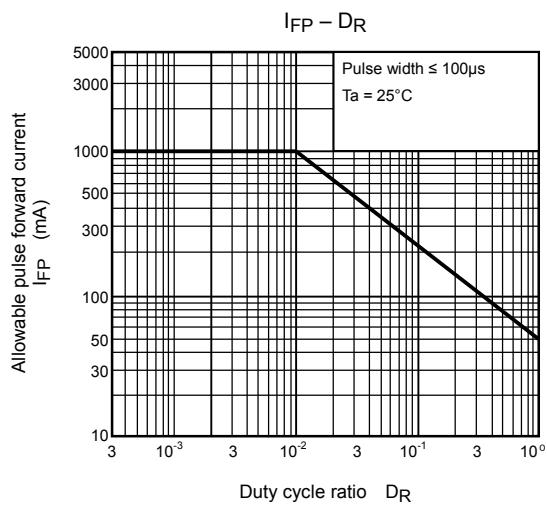
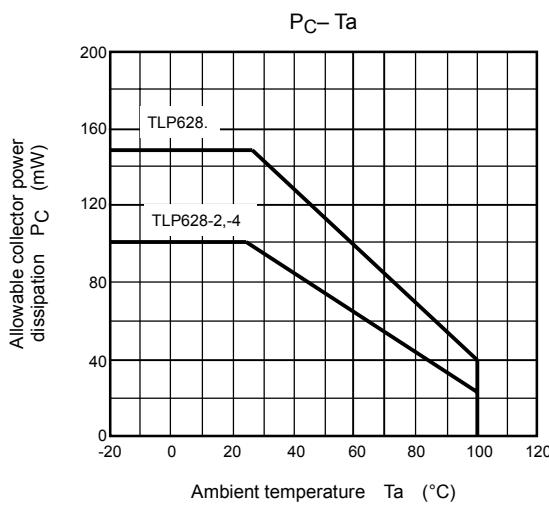
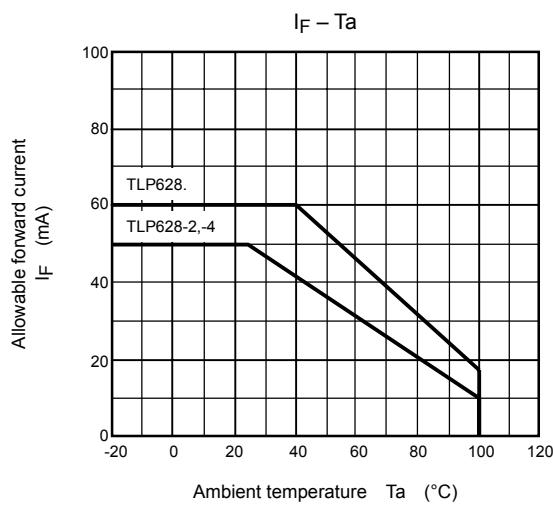
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C _S	V _S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R _S	V _S = 500 V R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation voltage	BVs	AC, 1 minute	5000	—	—	V _{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V _{dc}

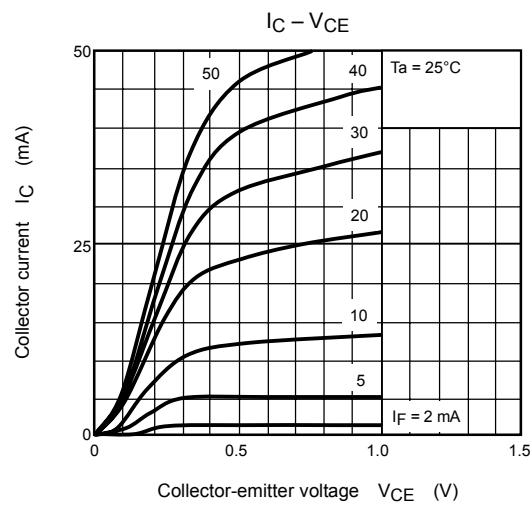
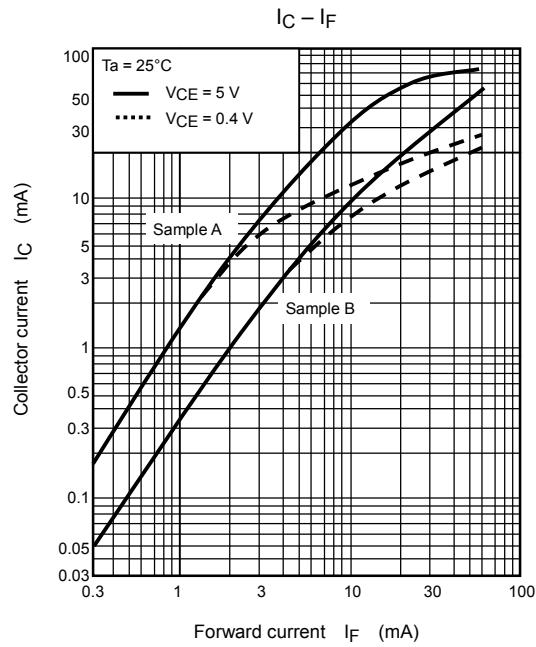
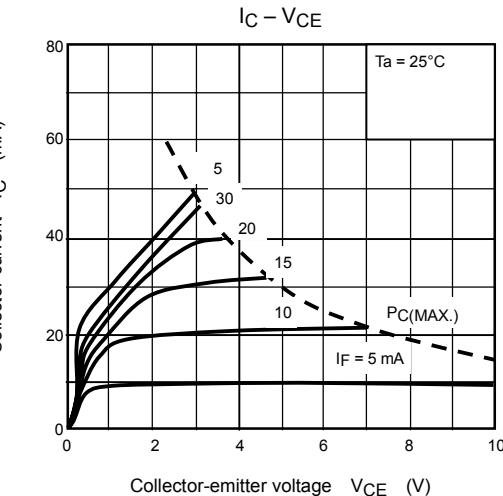
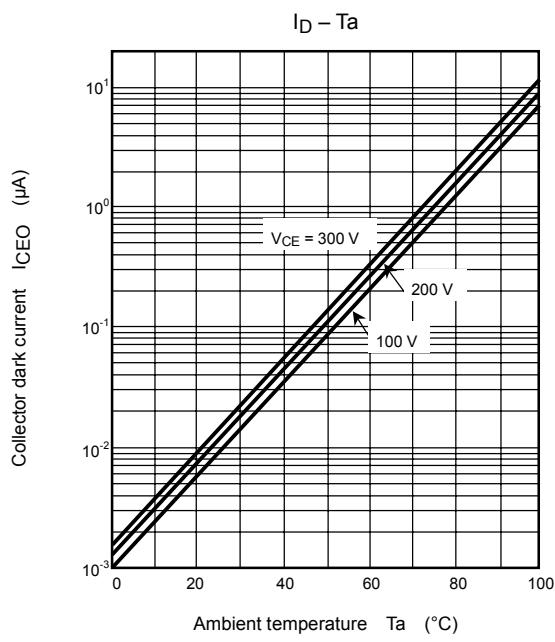
Switching Characteristics ($T_a = 25^\circ\text{C}$)

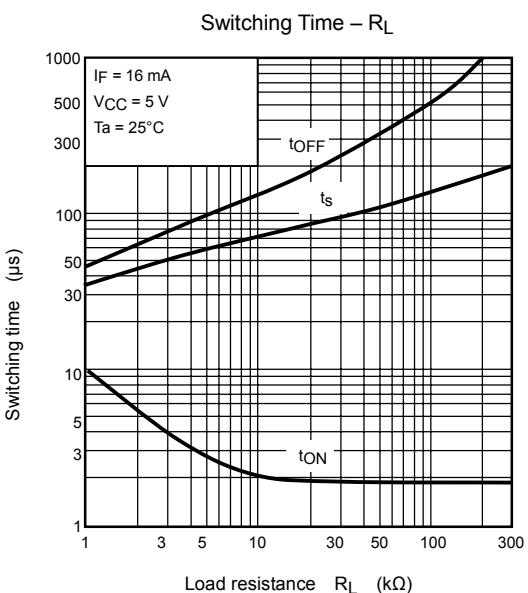
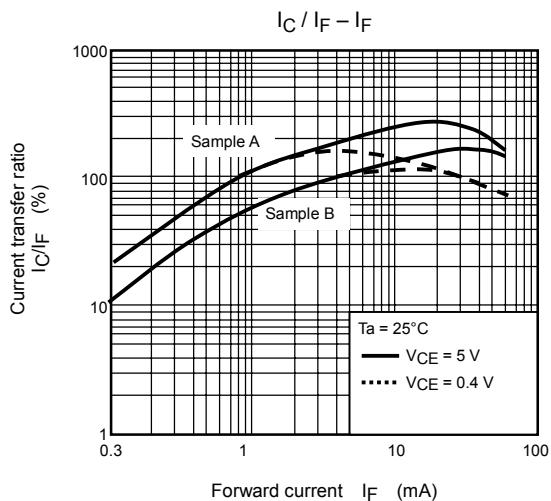
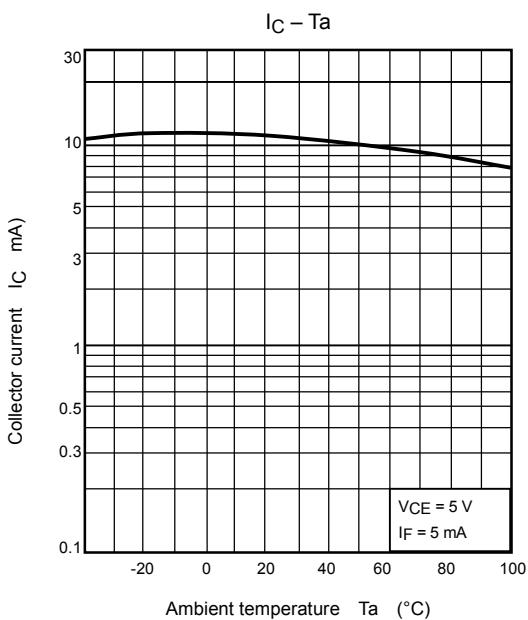
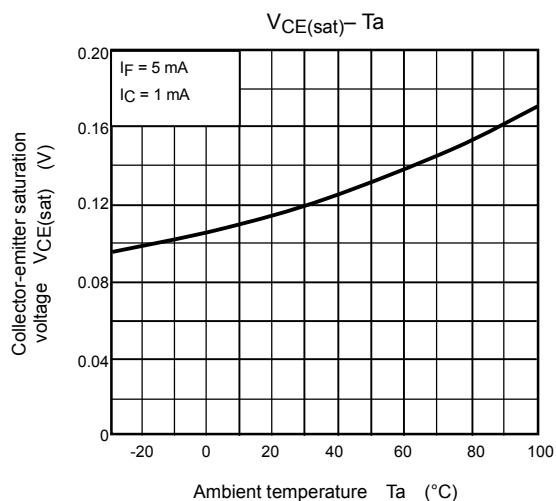
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t_r	$V_{CC} = 10\text{ V}, I_C = 2\text{ mA}$ $A_{RL} = 100\Omega$	—	2	—	μs
Fall time	t_f		—	3	—	
Turn-on time	t_{on}		—	3	—	
Turn-off time	t_{off}		—	3	—	
Turn-on time	t_{ON}	$R_L = 1.9\text{ k}\Omega$ (Fig.1) $V_{CC} = 5\text{ V}, I_F = 16\text{ mA}$	—	3	—	μs
Storage time	t_s		—	40	—	
Turn-off time	t_{OFF}		—	90	—	

Fig. 1 Switching time test circuit









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000707EBC

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